	Туре	L#	Hits	Search Text	DBs	Time Stamp	C o m m	ef in	Er ro rs
1	BRS	L1	9		USPAT; US-PG PUB; EPO; JPO; DERW ENT; IBM_T DB	2002/05/09 16:32			0
2	BRS	L8	0	etching same silicon same (SF6 and (Si2F6 or SiF4)) same anisotropic	USPAT; US-PG PUB; EPO; JPO; DERW ENT; IBM_T DB	2002/05/09 16:38			0
3	BRS	L15	0	etch\$3 same silicon same (SF6 and (Si2F6 or SiF4)) same anisotropic	USPAT; US-PG PUB; EPO; JPO; DERW ENT; IBM_T DB	2002/05/09 16:41			0
4	BRS	L22	40254	etch\$3 same silicon same (anisotropic or plasma or dry or rie or "reactive ion etching")	USPAT; US-PG PUB; EPO; JPO; DERW ENT; IBM_T DB	2002/05/09 16:43			0

	Туре	L#	Hits	Search Text	DBs	Time Stamp	C o m m	r D ef in	Er ro rs
5	BRS	L29	0	22 and 438/@.ccls.	, O, O,	2002/05/09 16:43			0
6	BRS	L36	16866	22 and 438/\$.ccls.	USPAT; US-PG PUB; EPO; JPO; DERW ENT; IBM_T DB	2002/05/09			0
7	BRS	L43	0	36 and @pd<=1996	USPAT; US-PG PUB; EPO; JPO; DERW ENT; IBM_T DB	2002/05/09 17:41			0
8	BRS	L50	7812	36 and @pd<=19960602	USPAT; US-PG PUB; EPO; JPO; DERW ENT; IBM_T DB	2002/05/09	***************************************		0

	Туре	L#	Hits	Search Text	DBs	Time Stamp	o m m e	D ef in iti	Er ro rs
9	BRS	L57	429	22 and 252/\$.ccls.	USPAT; US-PG PUB; EPO; JPO; DERW ENT; IBM_T DB	2002/05/09			0
10	BRS	L64	318	57 and @pd<=19960602	USPAT; US-PG PUB; EPO; JPO; DERW ENT; IBM_T DB	2002/05/09			0